

Vishay Semiconductors

RoHS

HALOGEN

FREE GREEN

Dome Lens SMD LED



DESCRIPTION

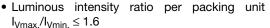
The dome lens SMD LED series has been designed in a small untinted and clear molded package with lens for surface mounting as gullwing or reverse gullwing version. The VLD.1235... series is using recent ultrabright AllnGaP / Si chip technology with high luminous flux and large chip size allowing a high DC forward current up to 70 mA.

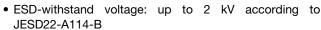
PRODUCT GROUP AND PACKAGE DATA

Product group: LED
Product series: power
Package: SMD dome lens
Angle of half intensity: ± 11°

FEATURES

- Utilizing latest advanced AllnGaP technology
- Package type: surface-mount
- Package form: gullwing, reverse gullwing
- Dimensions (L x W x H in mm): 2.3 x 2.3 x 2.8
- · High luminous flux and luminous intensity
- Luminous intensity and color categorized per packing unit





- Preconditioning according to JEDEC® level 2a
- Suitable for reflow soldering according to J-STD-020
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Traffic signals and signs
- Interior and exterior lighting
- Indicator and backlighting purposes for audio, video, LCDs switches, symbols, illuminated advertising etc.

PARTS TABLE FORWARD LUMINOUS WAVELENGTH at at INTENSITY **VOLTAGE PART** COLOR (nm) **TECHNOLOGY** ŀ le le (mcd) (V) (mA) (mA) (mA) MIN. TYP. MAX. MIN. MAX MIN. TYP. MAX. TYP. 11 000 VLDS1235G 5600 22 400 50 626 630 637 50 1.9 2.2 2.7 50 AllnGaP on Si Super red VLDS1235R Super red 5600 11 000 22 400 50 626 630 637 50 1.9 2.2 2.7 50 AllnGaP on Si VLDR1235G 9000 14 500 35 500 50 619 624 631 50 1.9 2.2 50 AllnGaP on Si Red 2.7 VLDR1235R Red 9000 14 500 35 500 50 619 624 631 50 1.9 2.2 2.7 50 AllnGaP on Si VLDK1235G Amber 9000 18 000 35 500 50 611 616 621 50 1.9 2.25 2.7 50 AllnGaP on Si VLDK1235R Amber 9000 18 000 35 500 50 611 616 621 50 1.9 2.25 2.7 50 AllnGaP on Si VLDY1235G Yellow 9000 18 000 35 500 50 583 589 595 50 1.9 2.3 2.7 50 AllnGaP on Si VLDY1235R 50 595 2.3 50 Yellow 9000 18 000 35 500 583 589 50 1.9 2.7 AllnGaP on Si VLDS1235G-08 5600 11 000 22 400 50 626 630 637 50 1.9 2.2 2.7 50 AllnGaP on Si Super red VLDS1235R-08 Super red 5600 11 000 22 400 50 626 630 637 50 1.9 2.2 2.7 50 AllnGaP on Si VLDR1235G-08 Red 9000 14 500 35 500 50 619 624 631 50 1.9 2.2 2.7 50 AllnGaP on Si VLDR1235R-08 Red 9000 14 500 35 500 50 619 624 631 50 1.9 2.7 50 AllnGaP on Si 2.2 VLDK1235G-08 9000 18 000 35 500 50 611 616 621 50 1.9 2.25 2.7 50 AllnGaP on Si Amber 35 500 50 621 50 VLDK1235R-08 Amber 9000 18 000 611 616 50 1.9 2.25 2.7 AllnGaP on Si VLDY1235G-08 Yellow 9000 18 000 35 500 50 583 589 595 50 1.9 2.3 2.7 50 AllnGaP on Si VLDY1235R-08 Yellow 9000 18 000 35 500 50 583 589 595 50 1.9 2.3 2.7 50 AllnGaP on Si

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ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified) VLDS1235, VLDR1235, VLDK1235, VLDY1235					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage (1)	Short term application only	V_R	5	V	
DC Forward current	T _{amb} ≤ 60 °C	I _F	70	mA	
Power dissipation		P _V	200	mW	
Junction temperature		Tj	125	°C	
Operating temperature range		T _{amb}	-40 to +100	°C	
Storage temperature range		T _{stg}	-40 to +100	°C	
Thermal resistance junction-to-ambient	Mounted on PC board (pad size > 16 mm ²)	R _{thJA}	325	K/W	

Note

⁽¹⁾ Driving the LED in reverse direction is suitable for a short term application only

OPTICAL AND ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified) VLDS1235G, VLDS1235R, SUPER RED						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Luminous intensity (1)	$I_F = 50 \text{ mA}$	I _V	5600	11 000	22 400	mcd
Luminous flux/luminous intensity		φ _V /I _V	-	0.5	-	mlm/mcd
Dominant wavelength (1)	I _F = 50 mA	λ_{d}	626	630	637	nm
Peak wavelength	I _F = 50 mA	λρ	-	639	-	nm
Spectral bandwidth at 50 % I _{rel max.}	$I_F = 50 \text{ mA}$	Δλ	-	18	-	nm
Angle of half intensity	$I_F = 50 \text{ mA}$	φ	-	± 11	-	deg
Forward voltage (1)	$I_F = 50 \text{ mA}$	V _F	1.9	2.2	2.7	V
Reverse current	V _R = 5 V	I _R	-	0.01	10	μA

Note

 $^{^{(1)}}$ Tolerances: \pm 15 % for $I_V,\,\pm$ 0.1 V for $V_F,\,\pm$ 1 nm for λ_d

OPTICAL AND ELECTRICAL CHARACTERISTICS ($T_{amb} = 25$ °C, unless otherwise specified) VLDR1235G, VLDR1235R, RED						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Luminous intensity (1)	I _F = 50 mA	I _V	9000	14 500	35 500	mcd
Luminous flux/luminous intensity		φ _V /I _V	-	0.5	-	mlm/mcd
Dominant wavelength (1)	I _F = 50 mA	λ_d	619	624	631	nm
Peak wavelength	$I_F = 50 \text{ mA}$	λ_{p}	-	632	-	nm
Spectral bandwidth at 50 % I _{rel max.}	$I_F = 50 \text{ mA}$	Δλ	-	18	-	nm
Angle of half intensity	$I_F = 50 \text{ mA}$	φ	-	± 11	-	deg
Forward voltage (1)	$I_F = 50 \text{ mA}$	V_{F}	1.9	2.2	2.7	V
Reverse current	V _R = 5 V	I _R	-	0.01	10	μΑ

Note

 $^{^{(1)}}$ Tolerances: \pm 15 % for $I_V,\,\pm$ 0.1 V for $V_F,\,\pm$ 1 nm for λ_d

OPTICAL AND ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified) VLDK1235G, VLDK1235R, AMBER						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Luminous intensity (1)	$I_F = 50 \text{ mA}$	I _V	9000	18 000	35 500	mcd
Luminous flux/luminous intensity		φ _V /I _V	=	0.5	-	mlm/mcd
Dominant wavelength (1)	$I_F = 50 \text{ mA}$	λ _d	611	616	621	nm
Peak wavelength	I _F = 50 mA	λρ	=	622	-	nm
Spectral bandwidth at 50 % I _{rel max} .	$I_F = 50 \text{ mA}$	Δλ	-	18	-	nm
Angle of half intensity	$I_F = 50 \text{ mA}$	φ	=	± 11	-	deg
Forward voltage (1)	$I_F = 50 \text{ mA}$	V _F	1.9	2.25	2.7	V
Reverse current	V _R = 5 V	I _R	-	0.01	10	μA

Note

 $^{^{(1)}~}$ Tolerances: \pm 15 % for $I_V,\,\pm$ 0.1 V for $V_F,\,\pm$ 1 nm for λ_d



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OPTICAL AND ELECTRICAL CHARACTERISTICS ($T_{amb} = 25 ^{\circ}C$, unless otherwise specified) VLDY1235G, VLDY1235R, YELLOW						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Luminous intensity (1)	$I_F = 50 \text{ mA}$	I _V	9000	18 000	35 500	mcd
Luminous flux/luminous intensity		φ _V /I _V	=	0.5	-	mlm/mcd
Dominant wavelength (1)	I _F = 50 mA	λ_{d}	583	589	595	nm
Peak wavelength	I _F = 50 mA	λ_{p}	=	591	-	nm
Spectral bandwidth at 50 % I _{rel max} .	I _F = 50 mA	Δλ		17		nm
Angle of half intensity	$I_F = 50 \text{ mA}$	φ		± 11		deg
Forward voltage (1)	I _F = 50 mA	V _F	1.9	2.3	2.7	V
Reverse current	V _R = 5 V	I _R		0.01	10	μΑ

Note

 $^{^{(1)}}$ Tolerances: \pm 15 % for $I_V,\,\pm$ 0.1 V for $V_F,\,\pm$ 1 nm for λ_d

COLOR CLASSIFICATION						
	DOMINANT WAVELENGTH (nm)					
GROUP	AMBER YELLOW			AMBER		LOW
	MIN.	MAX.	MIN.	MAX.		
2	611	616				
3	616	621	583	586		
4			586	589		
5			589	592		
6			592	595		

Note

• Wavelengths are tested at a current pulse duration of 25 ms and an accuracy of ± 1 nm

LUMINOUS INTENSITY CLASSIFICATION					
GROUP	LUMINOUS INTENSITY (mcd)				
STANDARD	MIN.	MAX.			
DB	5600	7100			
EA	7100	9000			
EB	9000	11 200			
FA	11 200	14 000			
FB	14 000	18 000			
GA	18 000	22 400			
GB	22 400	28 000			
HA	28 000	35 500			

Note

Luminous intensity is tested at a current pulse duration of 25 ms and an accuracy of ± 15 %.

The above type numbers represent the order groups which include only a few brightness groups. Only one group will be shipped on each reel (there will be no mixing of two groups on each reel).

In order to ensure availability, single brightness groups will not be orderable.

In a similar manner for colors where wavelength groups are measured and binned, single wavelength groups will be shipped on any one reel. In order to ensure availability, single wavelength groups will not be orderable

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TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

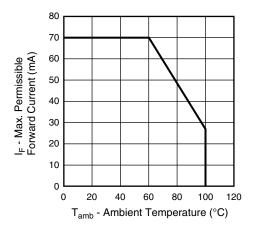


Fig. 1 - Maximum Permissible Forward Current vs.
Ambient Temperature

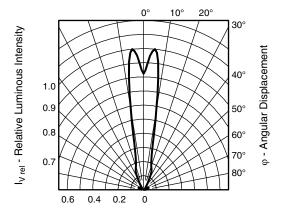


Fig. 2 - Relative Luminous Intensity vs. Angular Displacement

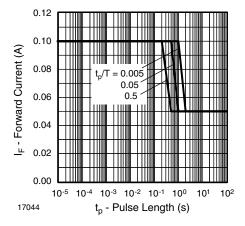


Fig. 3 - Forward Current vs. Pulse Length

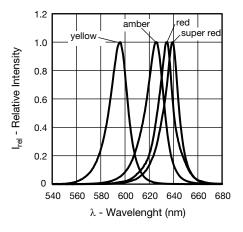


Fig. 4 - Relative Intensity vs. Wavelength

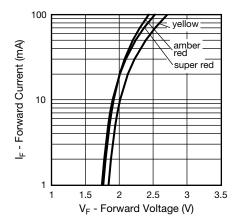


Fig. 5 - Forward Current vs. Forward Voltage

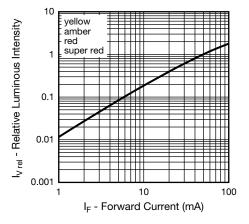


Fig. 6 - Relative Luminous Intensity vs. Forward Current

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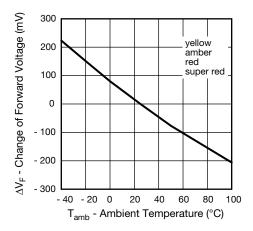


Fig. 7 - Change of Forward Voltage vs. Ambient Temperature

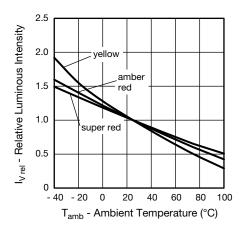


Fig. 8 - Relative Luminous Intensity vs. Ambient Temperature

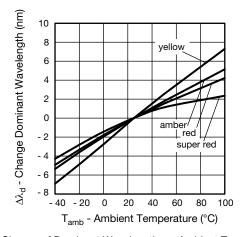
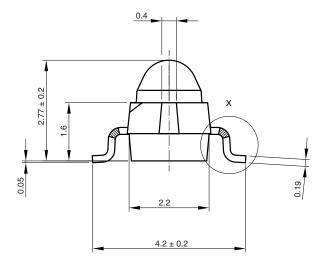
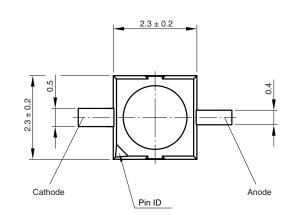


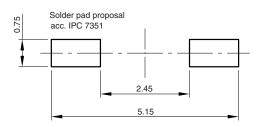
Fig. 9 - Change of Dominant Wavelength vs. Ambient Temperature

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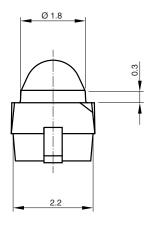
PACKAGE DIMENSIONS in millimeters: VLD.1235G.. (gullwing)

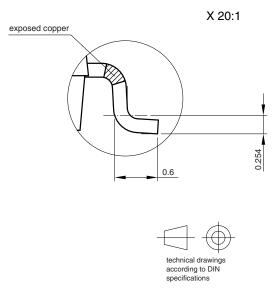






Drawing-No.: 6.544-5383.02-4 Issue: 4; 18.03.10 21488





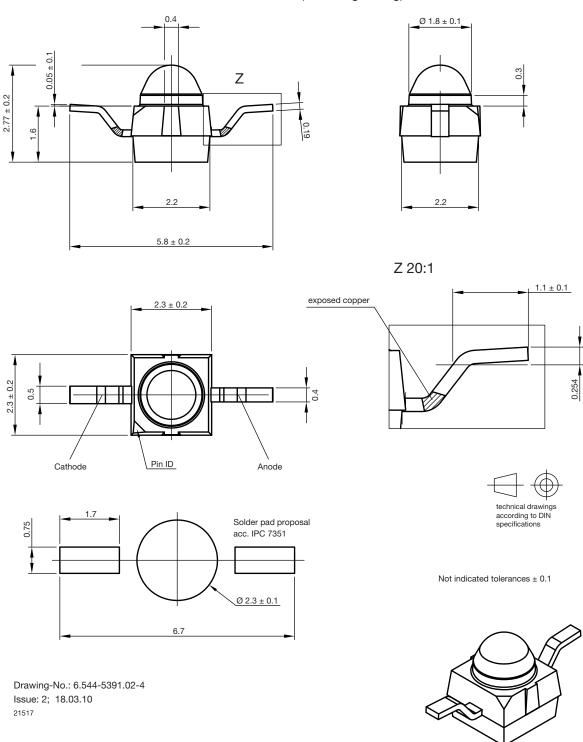


Not indicated tolerances ± 0.1



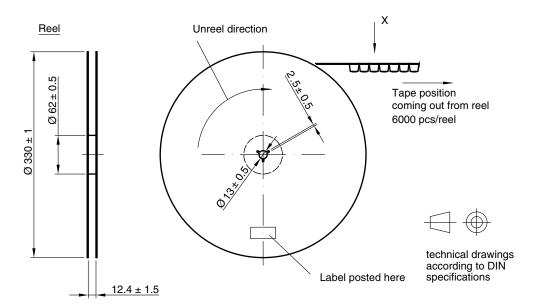
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PACKAGE DIMENSIONS in millimeters: VLD.1235R.. (reverse gullwing)

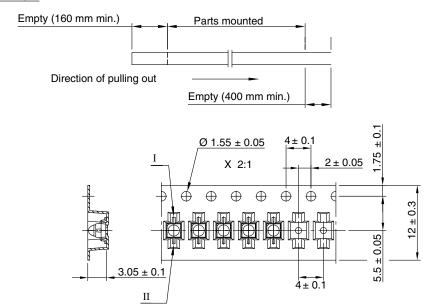


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TAPING AND REEL DIMENSIONS in millimeters: VLD.1235G (gullwing)



Leader and trailer tape:

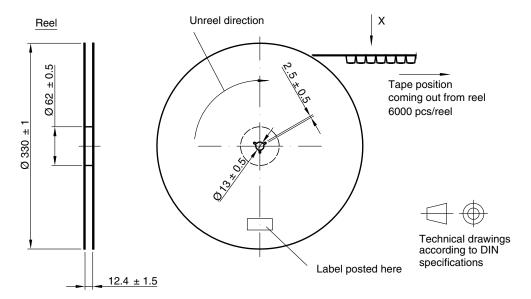


Drawing-No.: 9.800-5091.01-4

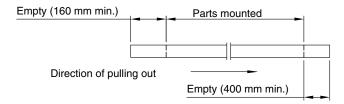
Issue: 3; 18.03.10

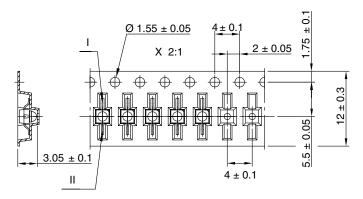
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TAPING AND REEL DIMENSIONS in millimeters: VLD.1235R (reverse gullwing)



Leader and trailer tape:



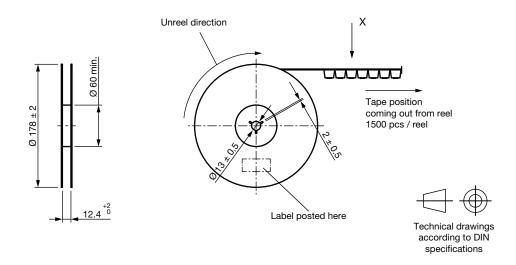


Drawing-No.: 9.800-5100.01-4

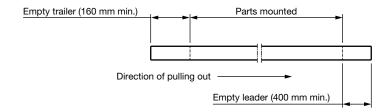
Issue: 2; 18.03.10

TAPING AND REEL DIMENSIONS in millimeters: VLD.1235G-08 (gullwing)

Reel



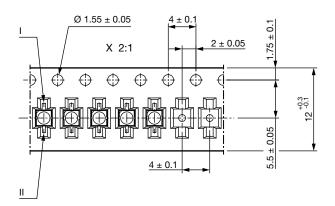
Leader and trailer tape



Terminal position in tape

Device	Lead I	Lead II	
VLDY153.G08			
VLDK153.G08	Cathode	Anode	
VLDR153.G08		Ariode	
VLDS153.G08			

3.05 ± 0.1

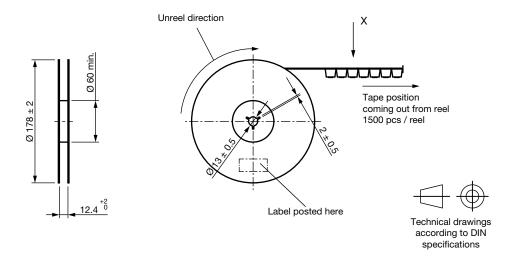


Drawing-No.: 9.800-5137.01-4

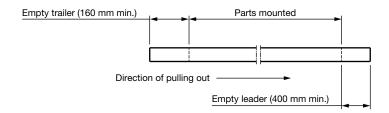
Issue: 1; 17.03.16

TAPING AND REEL DIMENSIONS in millimeters: VLD.1235R-08 (reverse gullwing)

Reel



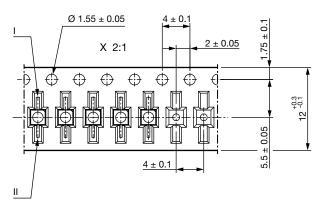
Leader and trailer tape



Terminal position in tape

Device	Lead I	Lead II
VLDY153.R08		
VLDK153.R08	Cathode	Anode
VLDR153.R08		Ariode
VLDS153.R08		

3.05 ± 0.1



Drawing-No.: 9.800-5138.01-4

Issue: 1; 17.03.16

COVER TAPE PEEL STRENGTH

According to DIN EN 60286-3 0.1 N to 1.3 N 300 ± 10 mm/min 165° to 180° peel angle

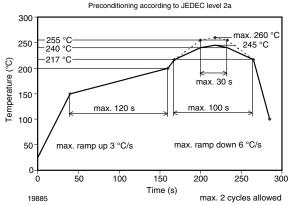
LABEL

Standard bar code labels for finished goods

The standard bar code labels are product labels and used for identification of goods. The finished goods are packed in final packing area. The standard packing units are labeled with standard bar code labels before transported as finished goods to warehouses. The labels are on each packing unit and contain Vishay Semiconductor GmbH specific data.

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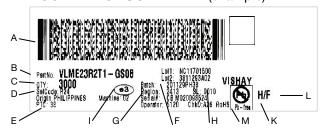
SOLDERING PROFILE



IR Reflow Soldering Profile for Lead (Pb)-Free Soldering

Fig. 10 - Vishay Lead (Pb)-free Reflow Soldering Profile (according to J-STD-020)

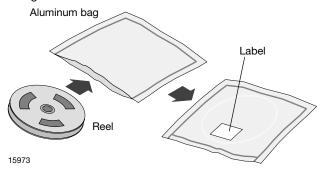
BAR CODE PRODUCT LABEL (example)



- A. 2D barcode
- B. PartNo = Vishay part number
- C. QTY = Quantity
- D. SelCode = selection code (binning)
- E. PTC = Code of manufacturing plant
- F. Batch = date code: year / week / plant code
- G. Region code
- H. SL = sales location
- I. Terminations finishing
- K. Lead (Pb)-free symbol
- L. Halogen-free symbol
- M. RoHS symbol

DRY PACKING

The reel is packed in an anti-humidity bag to protect the devices from absorbing moisture during transportation and



FINAL PACKING

The sealed reel is packed into a cardboard box. A secondary cardboard box is used for shipping purposes.

RECOMMENDED METHOD OF STORAGE

Dry box storage is recommended as soon as the aluminum bag has been opened to prevent moisture absorption. The following conditions should be observed, if dry boxes are not available:

- Storage temperature 10 °C to 30 °C
- Storage humidity ≤ 60 % RH max.

After more than 672 h under these conditions moisture content will be too high for reflow soldering.

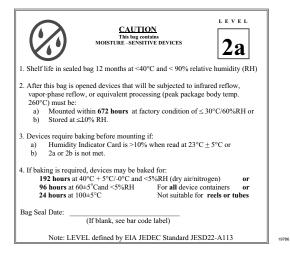
In case of moisture absorption, the devices will recover to the former condition by drying under the following condition:

192 h at 40 °C + 5 °C / - 0 °C and < 5 % RH (dry air / nitrogen) or

96 h at 60 °C + 5 °C and < 5 % RH for all device containers

24 h at 100 °C + 5 °C not suitable for reel or tubes.

An EIA JEDEC standard JESD22-A112 level 2a label is included on all dry bags.



Example of JESD22-A112 level 2a label

ESD PRECAUTION

Proper storage and handling procedures should be followed to prevent ESD damage to the devices especially when they are removed from the antistatic shielding bag. Electrostatic sensitive devices warning labels are on the packaging.

VISHAY SEMICONDUCTORS STANDARD **BAR CODE LABEL**

The Vishay Semiconductors standard bar code labels are printed at final packing areas. The labels are on each packing unit and contain Vishay Semiconductors specific data.



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